

*CLAIM AMENDMENTS*

Claim 1 (Cancelled).

2. (Currently Amended) ~~The A~~ method for manufacturing a semiconductor device ~~according to claim 1, wherein the mask material is~~ comprising:  
forming a film to be processed on a substrate;  
forming a metal film on the film to be processed;  
forming a resist pattern on the metal film;  
patterning the metal film using the resist pattern as a mask;  
shrinking the metal film after patterning;  
patterning the film to be processed using the metal film, after shrinking, as a mask;  
and  
removing the metal film.

3. (Currently Amended) The method for manufacturing a semiconductor device according to claim 2, ~~including forming wherein the metal film is a ruthenium film as the mask material, and including removing together the mask material, ruthenium film and the resist pattern in an oxygen-containing plasma.~~

4. (Previously Presented) A method for manufacturing a semiconductor device comprising :  
forming a film to be processed on a substrate;  
forming a ruthenium film as a mask material on the film to be processed;  
forming a resist pattern on the mask material;  
patterning the mask material using the resist pattern as a mask;  
patterning the film to be processed using the mask material, after  
patterning, as a mask; and  
removing the mask material.

5. (Previously Presented) The method for manufacturing a semiconductor device according to claim 4, including removing the mask material together with the resist pattern in an oxygen-containing plasma.

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6. (Previously Presented) The method for manufacturing a semiconductor device according to claim 5, including removing the mask material with a metal material exposed on the substrate.